Advanced Power MOSFET

SFM9120

FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10 μA (Max.) @ V_{DS} = -100V
- Lower $R_{DS(ON)}$: 0.444 Ω (Typ.)

BV_{DSS} = -100 V
$R_{DS(on)}$ = 0.6 Ω
I_D = -1.7 A

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1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	-100	V
I_D	Continuous Drain Current (T_A=25°C)	-1.7	A
	Continuous Drain Current (T_A=70°C)	-1.1	
I_{DM}	Drain Current-Pulsed ①	-13.6	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy ②	12	mJ
I_{AR}	Avalanche Current ①	-1.7	A
E_{AR}	Repetitive Avalanche Energy ①	0.39	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-6.5	V/ns
P_D	Total Power Dissipation (T_A=25°C) * Linear Derating Factor *	3.9 0.031	W W/°C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient *	--	32	°C/W

* When mounted on the minimum pad size recommended (PCB Mount).

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Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	-100	--	--	V	V_{GS}=0V,I_D=-250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	-0.1	--	V/°C	I_D=-250μA *See Fig 7*
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	--	-4.0	V	V_{DS}=-5V,I_D=-250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	-100	nA	V_{GS}=-20V
	Gate-Source Leakage , Reverse	--	--	100		V_{GS}=20V
I_{DSS}	Drain-to-Source Leakage Current	--	--	-10	μA	V_{DS}=-100V
		--	--	-100		V_{DS}=-80V,T_C=125°C
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.6	Ω	V_{GS}=-10V,I_D=-0.85A ④
g_{fs}	Forward Transconductance	--	2.0	--	℧	V_{DS}=-40V,I_D=-0.85A ④
C_{iss}	Input Capacitance	--	425	550	pF	V_{GS}=0V,V_{DS}=-25V,f =1MHz *See Fig 5*
C_{oss}	Output Capacitance	--	90	135		
C_{rss}	Reverse Transfer Capacitance	--	31	45		
$t_{d(on)}$	Turn-On Delay Time	--	11	30	ns	V_{DD}=-50V,I_D=-6A, R_G=18 Ω *See Fig 13* ④⑤
t_r	Rise Time	--	21	50		
$t_{d(off)}$	Turn-Off Delay Time	--	34	80		
t_f	Fall Time	--	18	45		
Q_g	Total Gate Charge	--	16	20	nC	V_{DS}=-80V,V_{GS}=-10V, I_D=-6A *See Fig 6 & Fig 12* ④⑤
Q_{gs}	Gate-Source Charge	--	3.1	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	6.3	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	-1.7	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	-13.6		
V_{SD}	Diode Forward Voltage ④	--	--	-3.8	V	T_J=25°C,I_S=-1.7A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	105	--	ns	T_J=25°C,I_F=-6A
Q_{rr}	Reverse Recovery Charge	--	0.4	--	μC	di_F/dt=100A/μs ④

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
② L=6.0mH, I_{AS}=-1.7A, V_{DD}=-25V, R_G=27Ω*, Starting T_J =25°C
③ $I_{SD} \leq$ -6A, di/dt ≤ 350A/μs, $V_{DD} \leq BV_{DSS}$, Starting T_J =25°C
④ Pulse Test : Pulse Width = 250μs, Duty Cycle ≤ 2%
⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

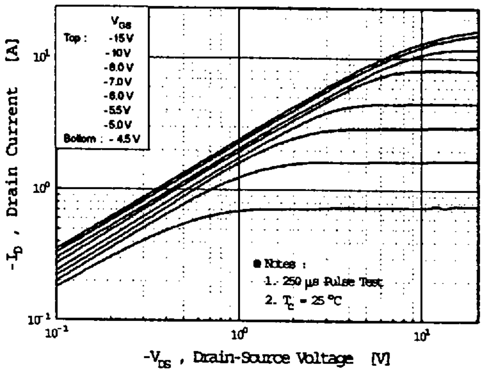

Fig 2. Transfer Characteristics

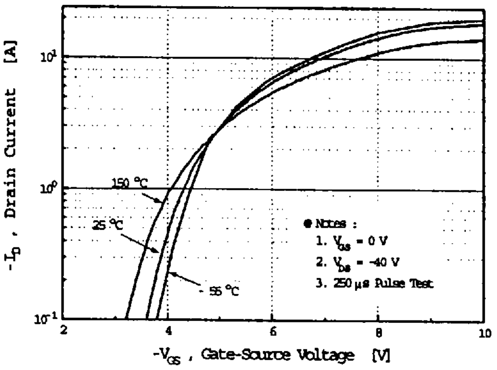

Fig 3. On-Resistance vs. Drain Current

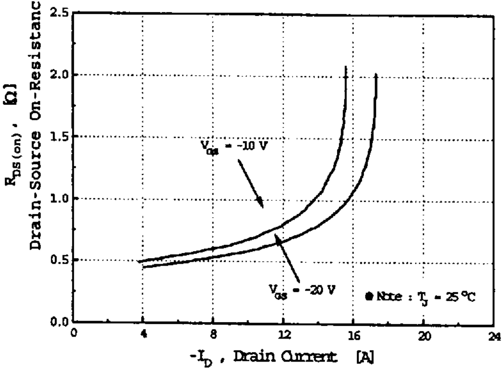

Fig 4. Source-Drain Diode Forward Voltage

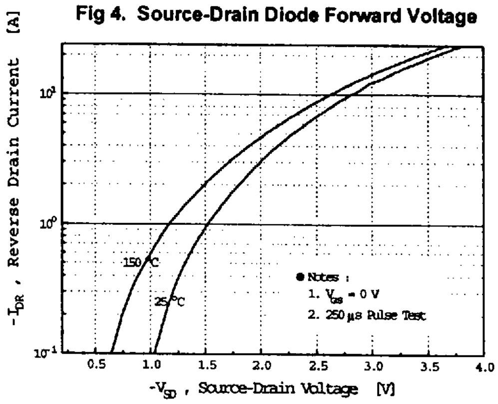

Fig 5. Capacitance vs. Drain-Source Voltage

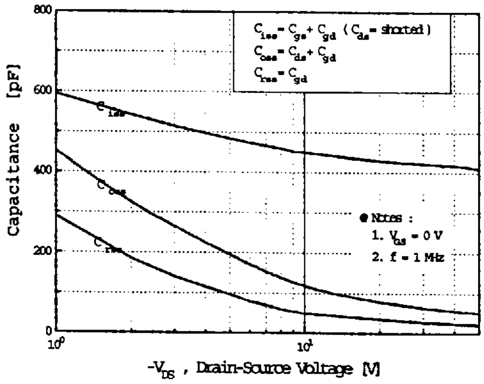

Fig 6. Gate Charge vs. Gate-Source Voltage

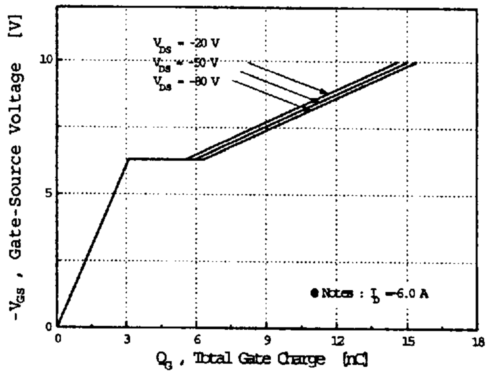

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Fig 7. Breakdown Voltage vs. Temperature

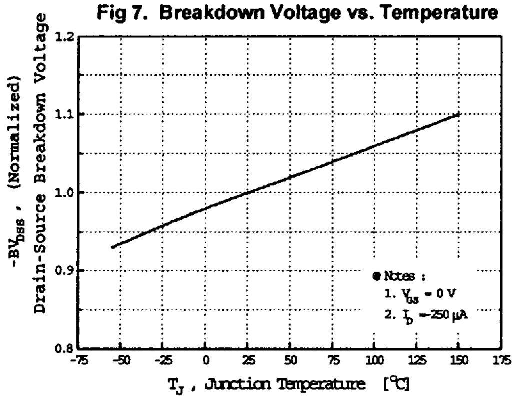


Fig 8. On-Resistance vs. Temperature

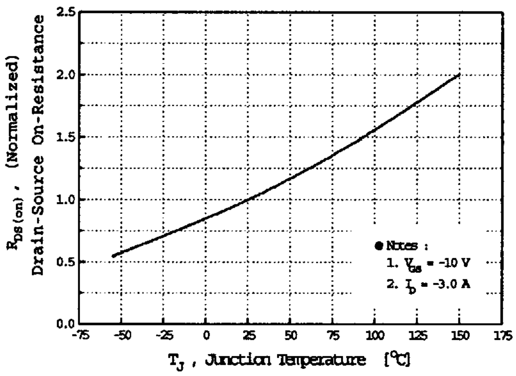


Fig 9. Max. Safe Operating Area

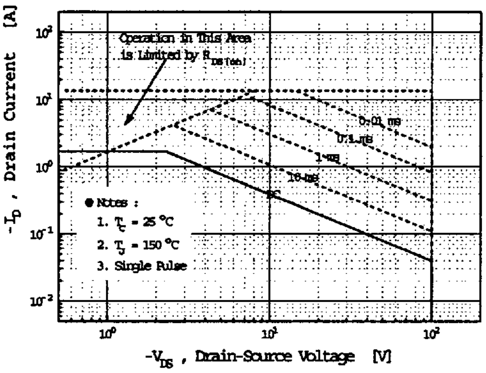


Fig 10. Max. Drain Current vs. Case Temperature

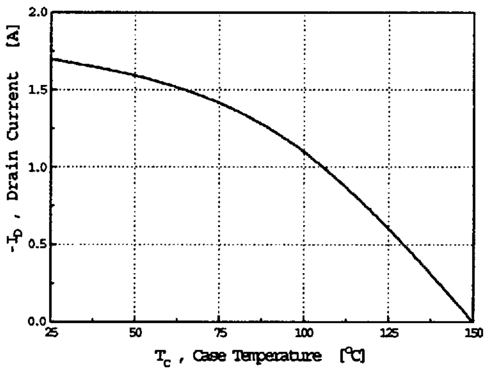


Fig 11. Thermal Response

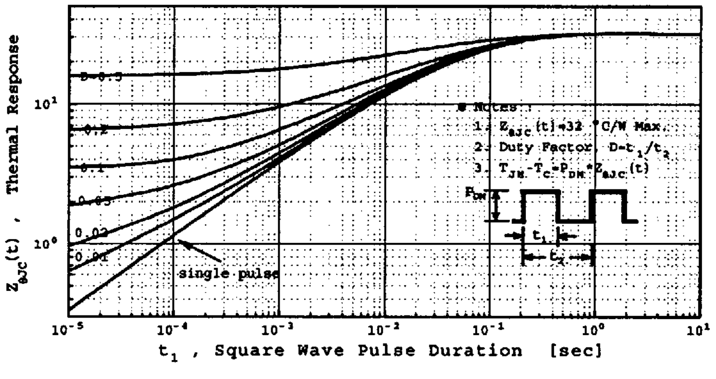


Fig 12. Gate Charge Test Circuit & Waveform

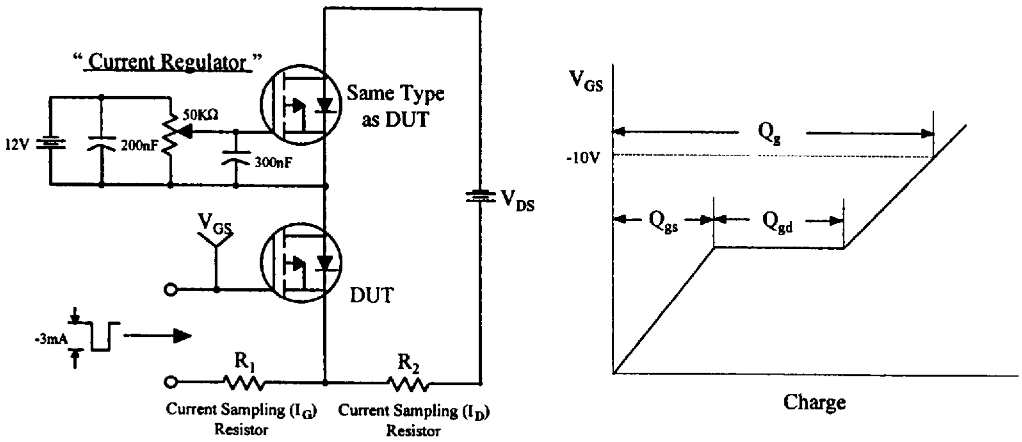


Fig 13. Resistive Switching Test Circuit & Waveforms

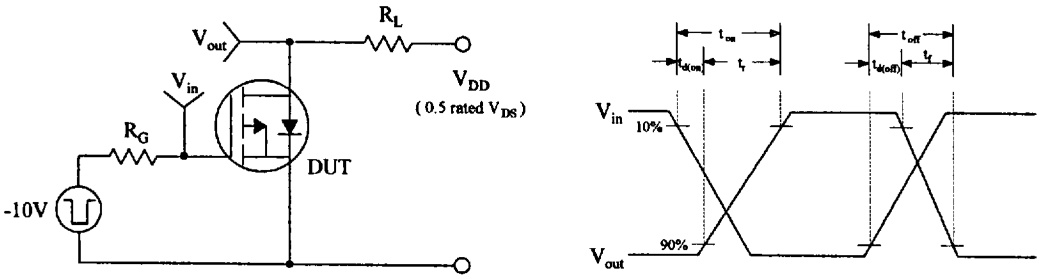


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

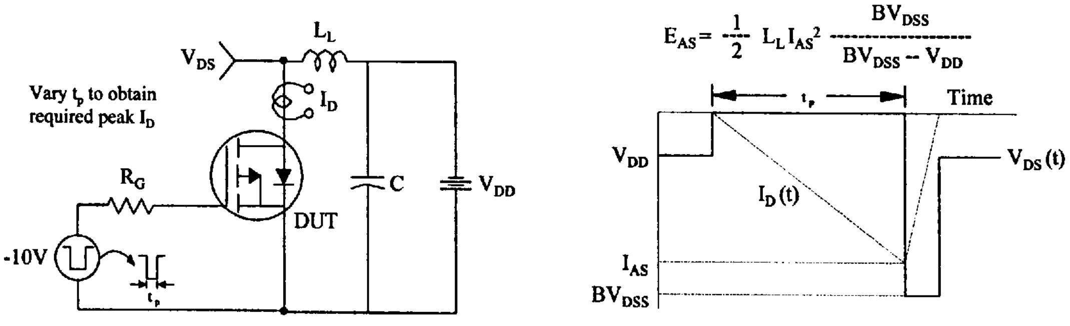
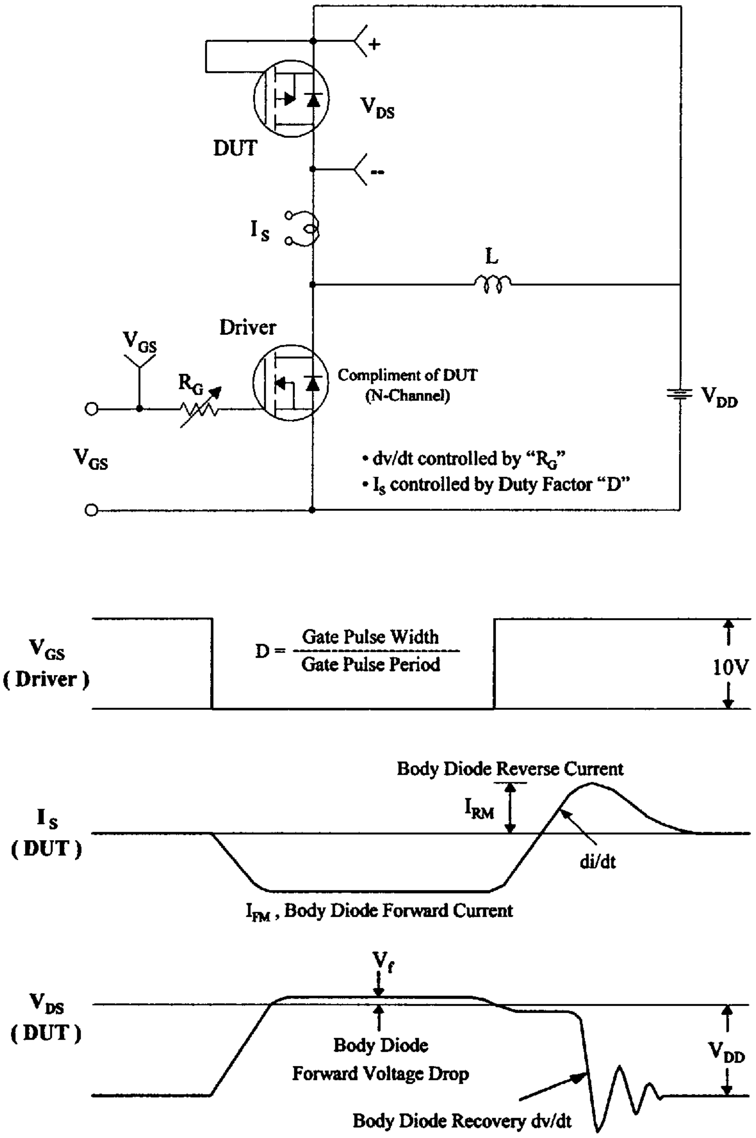

$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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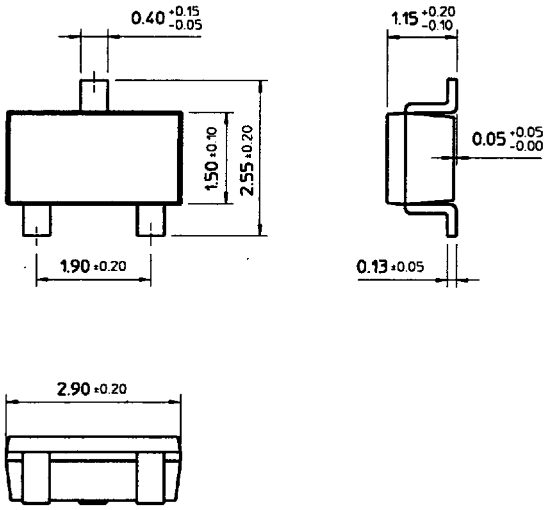

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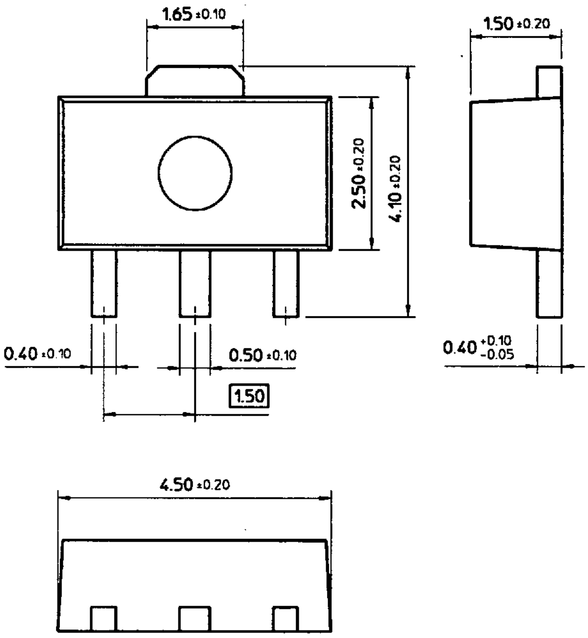

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